

# High efficiency Hetero-Junction: from pilot line to industrial production

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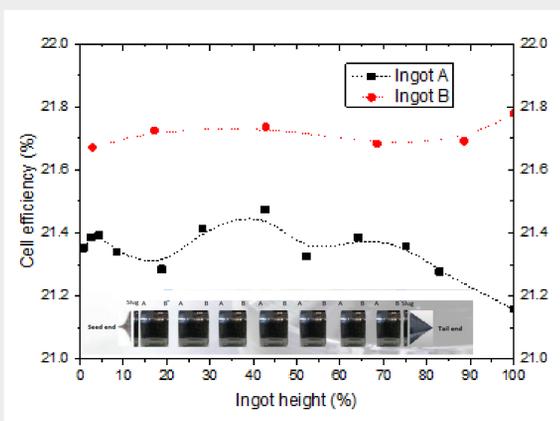
## Context

Silicon heterojunction (SHJ) technology allow to reach an efficiency of 26% [1]. Enel Green Power (EGP) is the ENEL company focused on production of energy by renewable and sustainable sources and already produced more than 6 million of thin film silicon PV. Recently EGP has started the 3SUN 2.0 program for the development and manufacturing of HJT cells and modules by converting its facilities, in close partnership with CEA-INES. The HJT technology allows to achieve higher efficiency solar cells with high bifacial factor. The combination of high efficiency and bifacial factor will enable EGP-3SUN HJT solar cells to compete on the market due to the low achievable LCOE in the utility scale segment.

## Material Selection

Studies have been performed at CEA-INES pilot line to evaluate the impact of wafers properties on cell efficiencies:

- Ingots A - res: 1 – 7  $\Omega$ .cm;  $\tau > 2$  ms
- Ingots B - res: 0.2 - 2  $\Omega$ .cm;  $\tau > 500$   $\mu$ s



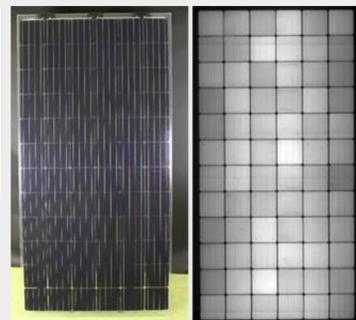
Cells efficiencies with 4 busbars cell design of 21.3% (ingot A) and 21.7% (ingot B) are quite stable over all the height. A clear step of 0.35% is attributed to different bulk material properties.

## Modules efficiency

Bifacial SHJ modules made and measured on flash-tester at CEA-INES with dark background and electroluminescence (EL) [4].

Side	Pmax (Wc)	Voc (V)	Isc (A)	FF (%)
Front side	380,7	53,4	9,15	77,9
Back side	331,5	53,3	7,95	78,2

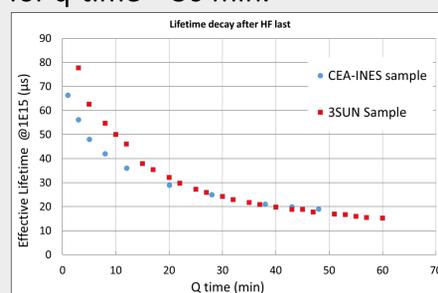
No defects (crack, dark spots) are visible.



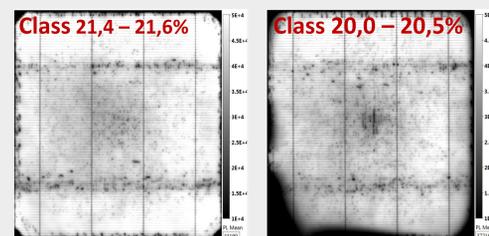
## Manufacturing aspects towards high efficiency HJT production

Fully automated production line with covered conveyors, clean environment and reduced human intervention:

Automatic N<sub>2</sub> buffer :  
→ prevent surface oxidation for q-time > 30 min.

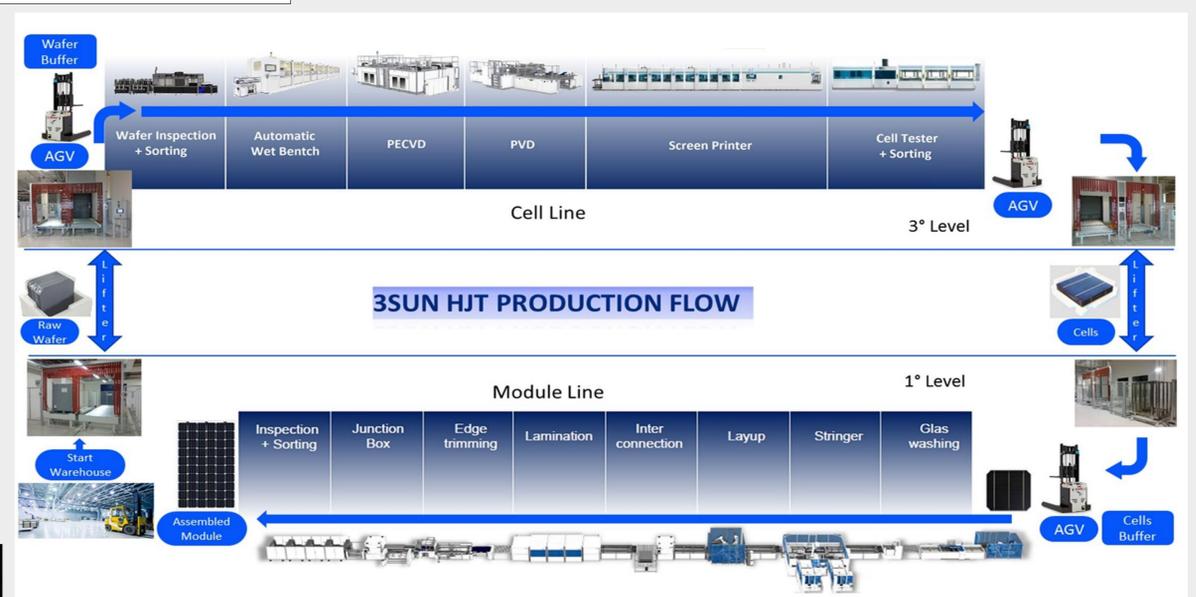


On line PL equipment:  
→ wafers defective regions monitoring [3]



Gentle wafer handling:  
→ reduce belt marks or rubbing

Innovative cell layout:  
→ save silver paste and reducing shadowing.



Integrated EL:  
→ control stringer and lamination process.

MES complete integration:  
→ Control process through SPC, DOE and data correlation  
→ Cells traceability using wafer virtual ID  
→ Material traceability  
→ OEE analysis  
→ Data mining

## Conclusion & Perspectives

Strong collaboration between EGP and CEA-INES produced very good results on the deployment of SHJ technology at large production scale. Pre-production tests to evaluate the impact of wafers properties on cell efficiencies have been performed at CEA-INES pilot line. Results demonstrates material quality has strong effect on cell efficiency. EGP-3SUN 2.0 fully automated line is designed to ensure high efficiency bifacial HJT panels production at a large scale.

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 [4] A. Battaglia, W. Favre et al., proceedings of the EU PVSEC, 2017